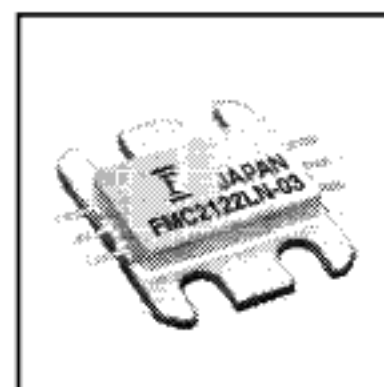


### FEATURES

- High Output Power:  $P_{1dB} = 12dBm(Typ.)$
- High Gain:  $G_{1dB} = 12dB(Typ.)$
- Low In/Out VSWR
- Low Noise:  $NF = 3.0dB (Typ.)$
- Broad Band: 21.2 ~ 22.4GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package (12 X 15 X 3.5mm)



### DESCRIPTION

The FMC2122LN-03 is a module that contains a two-stage amplifier, internally matched, for standard communications in the 21.2 to 22.4GHz frequency range. This product is well suited for point-to-point radio applications as it offers high power, high gain, low VSWR and low noise.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATINGS (Ambient Temperature $T_a = 25^\circ C$ )

Parameter	Symbol	Rating	Unit
DC Input Voltage	$V_{DD}$	10	V
DC Input Voltage	$V_{GG}$	-7	V
Input Power	$P_{in}$	3	dBm
Storage Temperature	$T_{stg}$	-55 to +125	$^\circ C$
Operating Case Temperature	$T_{op}$	-55 to +85	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs modules:

1. The drain operating voltage ( $V_{DD}$ ) should not exceed 8 volts.
2. The gate operating voltage ( $V_{GG}$ ) should not exceed -5 volts.

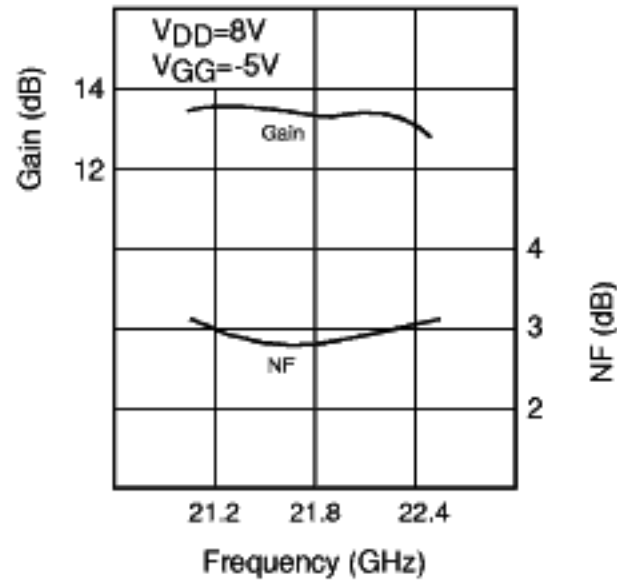
### ELECTRICAL CHARACTERISTICS (Case Temperature $T_c = 25^\circ C$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Frequency Range	$f$		21.2 ~ 22.4			GHz
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DD} = 8V$ $V_{GG} = -5V$ $f = 21.2 \sim 22.4 GHz$	11.0	12.0	-	dBm
Power Gain at 1 dB G.C.P.	$G_{1dB}$		11.0	12.0	-	dB
Noise Figure	NF		-	3.0	4.0	dB
Gain Flatness	G	$V_{DD} = 8V$ $V_{GG} = -5V$ $P_{in} = -15dBm$ $f = 21.2 \sim 22.4GHz$	-	1.0	-	dB
Input VSWR	$VSWR_i$		-	3.0:1	-	-
Output VSWR	$VSWR_o$		-	2.5:1	-	-
DC Input Current	$I_D$	$V_{DD} = 8V$ $V_{GG} = -5V$	-	40	70	mA
DC Input Current	$I_G$		-	10	15	mA

CASE STYLE: GJ

G.C.P.: Gain Compression Point

GAIN & NF vs. FREQUENCY



Case Style "GJ"  
Metal-Ceramic Hermetic Package

